

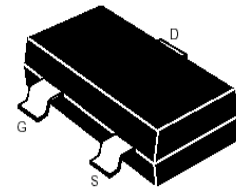
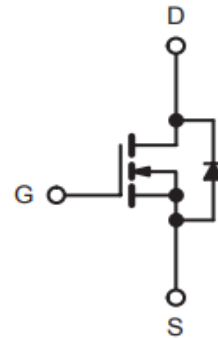
»Features

$V_{DS} = 30V$   
 $I_D = 5A$   
 $R_{DS(ON)} @V_{GS} = 10V, TYP = 45m\Omega$   
 $R_{DS(ON)} @V_{GS} = 4.5V, TYP = 55m\Omega$

»General Description

- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance
- SOT-23 for Surface Mount Package.

»Pin Configurations



»Absolute Maximum Ratings @ $T_A=25^\circ C$  unless otherwise noted

Characteristic	Symbol	Max	Unit
Drain-Source Voltage	$BV_{DSS}$	30	V
Gate- Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current (continuous)	$I_D$	5	A
Drain Current (pulsed)	$I_{DM}$	15	A
Total Device Dissipation $T_A=25^\circ C$	$P_D$	1250	mW
Junction	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55to+150	$^\circ C$

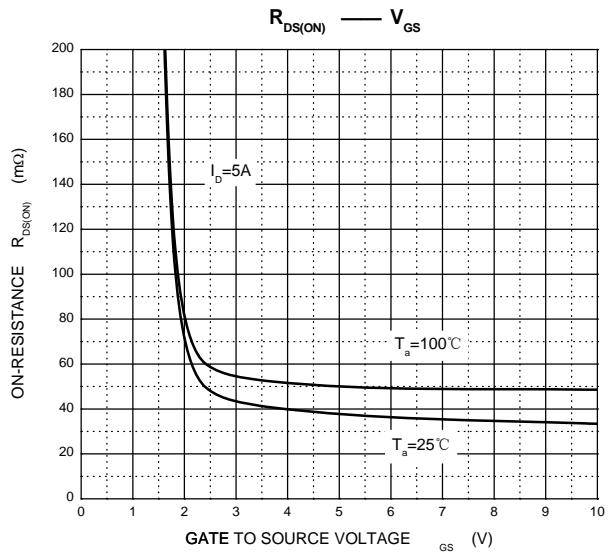
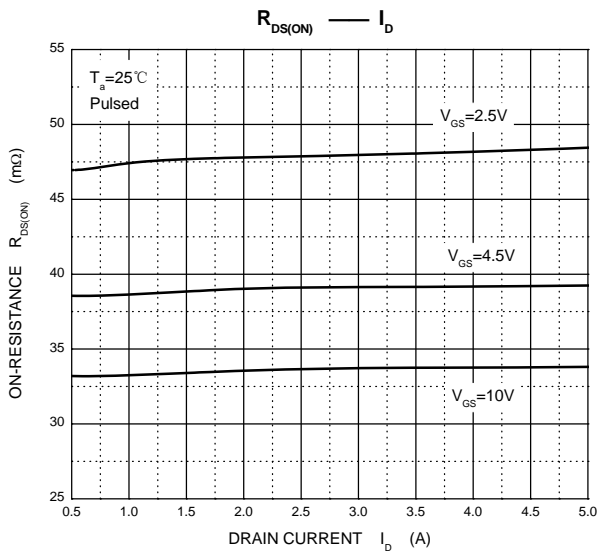
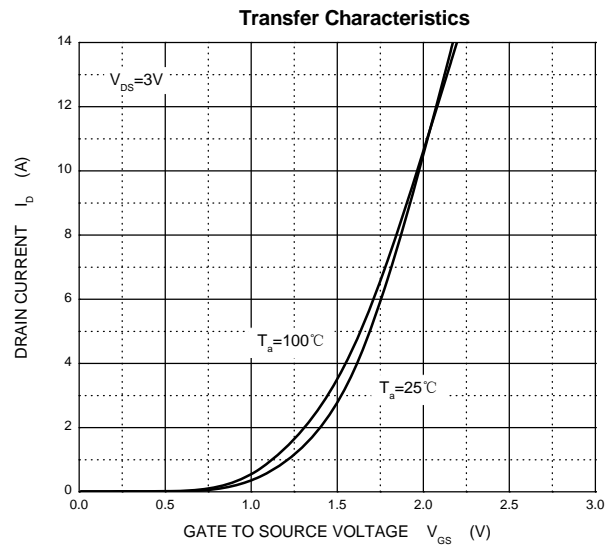
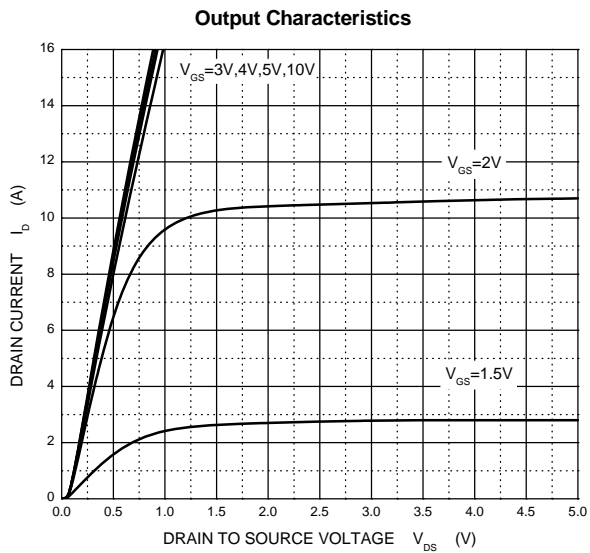
**»Electrical Characteristics @ $T_A=25^{\circ}\text{C}$  unless otherwise noted**

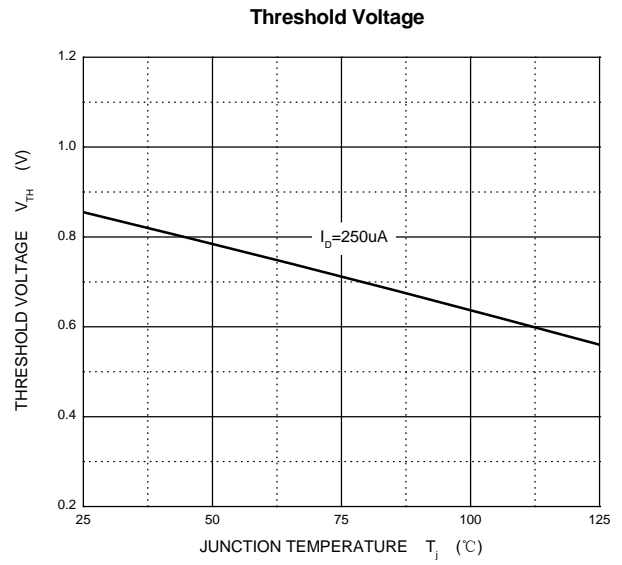
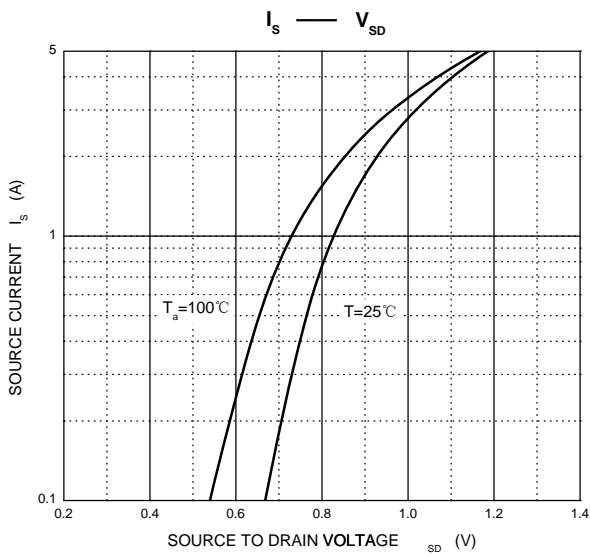
Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage ( $I_D = 250\mu\text{A}, V_{GS}=0\text{V}$ )	$BV_{DSS}$	30	—	—	V
Gate Threshold Voltage ( $I_D = 250\mu\text{A}, V_{GS}=V_{DS}$ )	$V_{GS(th)}$	0.6	—	2	V
Diode Forward Voltage Drop ( $I_S = 1\text{A}, V_{GS}=0\text{V}$ )	$V_{SD}$	—	—	1	V
Zero Gate Voltage Drain Current ( $V_{GS}=0\text{V}, V_{DS}=24\text{V}$ )	$I_{DSS}$	—	—	1	$\mu\text{A}$
Gate Body Leakage ( $V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V}$ )	$I_{GSS}$	—	—	$\pm 100$	nA
Static Drain-Source On-State Resistance ( $I_D = 4\text{A}, V_{GS}=10\text{V}$ )	$R_{DS(ON)}$	—	45	55	$\text{m}\Omega$
Static Drain-Source On-State Resistance ( $I_D = 3\text{A}, V_{GS}=4.5\text{V}$ )	$R_{DS(ON)}$	—	55	70	$\text{m}\Omega$
Static Drain-Source On-State Resistance ( $I_D = 2\text{A}, V_{GS}=2.5\text{V}$ )	$R_{DS(ON)}$	—	83	110	$\text{m}\Omega$
Input Capacitance ( $V_{GS}=10\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$ )	$C_{ISS}$	—	235	—	pF
Output Capacitance ( $V_{GS}=10\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$ )	$C_{OSS}$	—	35	—	pF
Turn-ON Time ( $V_{DS}=15\text{V}, V_{GS}=10\text{V}, R_{GEN}=6\Omega$ )	$t_{(on)}$	—	3.5	—	ns
Turn-OFF Time ( $V_{DS}=15\text{V}, V_{GS}=10\text{V}, R_{GEN}=6\Omega$ )	$t_{(off)}$	—	17.5	—	ns

**Notes :**

 \*Pulse Test : Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

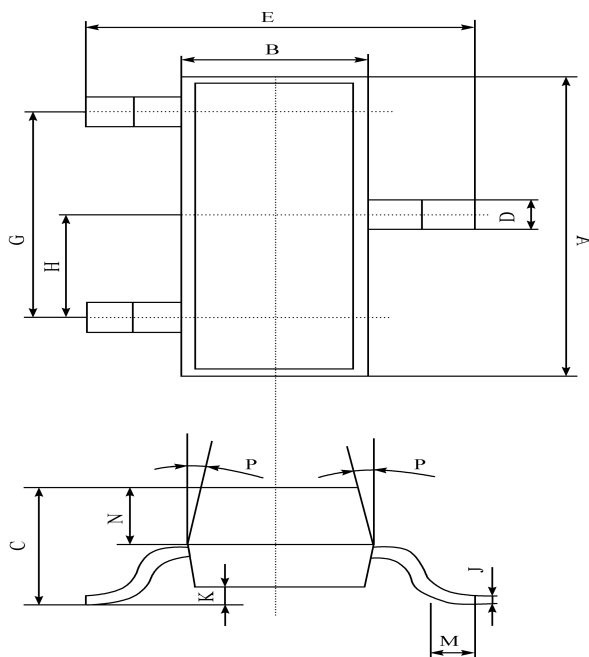
»Typical Performance Characteristics (T<sub>J</sub> = 25 °C, unless otherwise noted)





»Package Information

SOT-23



A	$2.90 \pm 0.10$
B	$1.30 \pm 0.10$
C	$1.00 \pm 0.10$
D	$0.40 \pm 0.10$
E	$2.40 \pm 0.20$
G	$1.90 \pm 0.10$
H	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	$0.00 - 0.10$
M	$\geq 0.2$
N	$0.60 \pm 0.10$
P	$7 \pm 2^\circ$

»Ordering information

Order code	Package	Marking	Base qty	Delivery mode
AO3402	SOT-23	WT3H	3K	Tape and reel

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Bourne](#) manufacturer:*

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [AOD464](#)  
[2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#)  
[IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#)  
[EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#)  
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#)  
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#)  
[C3M0021120D](#) [DMN6022SSD-13](#)